Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	891	349/38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S2	291	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:31
S3	2397	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:31
S4	1718	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:31
S5	366	349/46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:32
S6	1672	349/158	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:32
S7	5749	S1 or S2 or S3 or S4 or S5 or S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:32
S8	168	349/160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:33
S9	5855	S7 or S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:33
S10	62	S7 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:33

S11	0	S10 and (gate or scan$4) and (data or signal$4) and source and drain and pixel and electrode and ((thin near3 film) or tft) and ((storage near3 capacit$5) near6 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S12	934	S9 and (gate or scan$4) and (data or signal$4) and source and drain and pixel and electrode and ((thin near3 film) or tft) and (storage near3 capacit$5) and (semiconductor or active) and insulat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 12:36
S13	89	S12 and (substrate near6 (rough or protru$6 or depress$4 or convex or concave or bump$3 or dot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 09:17
S14	16	S13 and lattice	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 09:28
S15	168	349/160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 09:17
S16	48	S15 and (substrate near6 (rough or protru$6 or depress$4 or convex or concave or bump$3 or dot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 09:17
S17	7	S15 and lattice	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/22 09:28
S18	972	349/141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S19	1524	349/143	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S20	895	349/38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50

S21	291	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S22	2401	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S23	1728	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S24	367	349/46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S25	1673	349/158	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S26	5763	S20 or S21 or S22 or S23 or S24 or S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S27	169	349/160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S28	5870	S26 or S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S29	7382	S18 or S19 or S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:50
S30	158	S29 and (gate or scan$4) and (data or signal$4) and source and drain and pixel and electrode and ((thin near3 film) or tft) and ((storage near3 capacit$5) near6 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 12:54

S31	8	("4145120" | "5028122" | "5187602" | "5193017" | "5206749" | "5231039" | "5233448" | "5339181").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/23 13:01
S32	169	349/160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/23 14:08